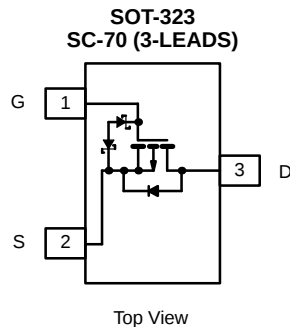




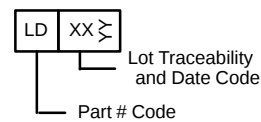
P-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-20	0.430 @ $V_{GS} = -4.5$ V	± 0.72
	0.480 @ $V_{GS} = -3.6$ V	± 0.68
	0.700 @ $V_{GS} = -2.5$ V	± 0.56

ESD Protected
3000 V

Marking Code

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	5 secs	Steady State	Unit
Drain-Source Voltage		V_{DS}	−20		V
Gate-Source Voltage		V_{GS}	± 12		
Continuous Drain Current ($T_J = 150^{\circ}\text{C}$) ^a	$T_A = 25^{\circ}\text{C}$	I_D	± 0.72	± 0.67	A
	$T_A = 70^{\circ}\text{C}$		± 0.58	± 0.54	
Pulsed Drain Current		I_{DM}	± 2.5		
Continuous Diode Current (Diode Conduction) ^a		I_S	−0.28	−0.24	
Maximum Power Dissipation ^a	$T_A = 25^{\circ}\text{C}$	P_D	0.34	0.29	W
	$T_A = 70^{\circ}\text{C}$		0.22	0.19	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	−55 to 150		$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{thJA}	315	375	$^\circ\text{C/W}$
	Steady State		360	430	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	285	340	

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

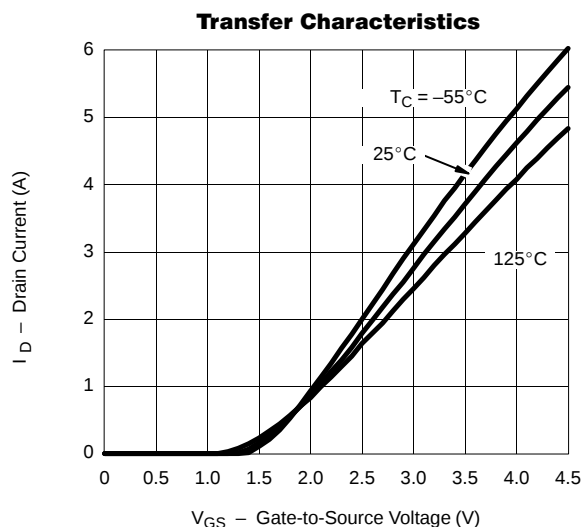
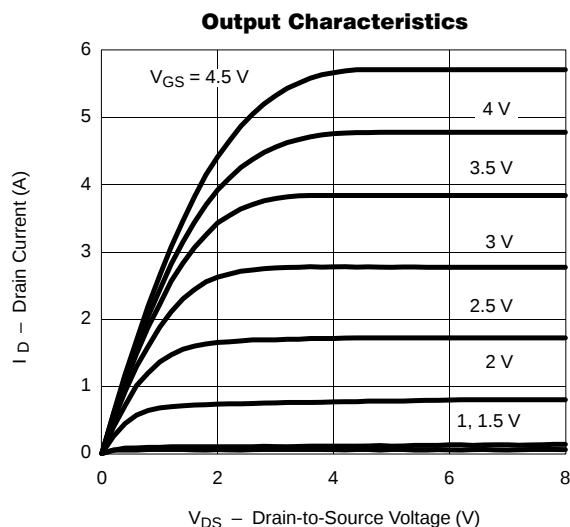
SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

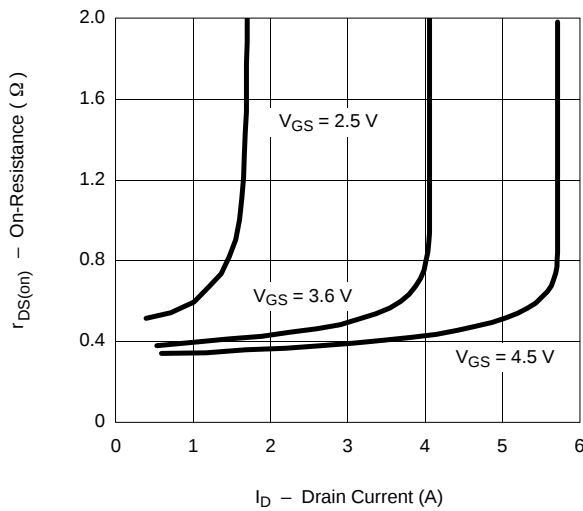
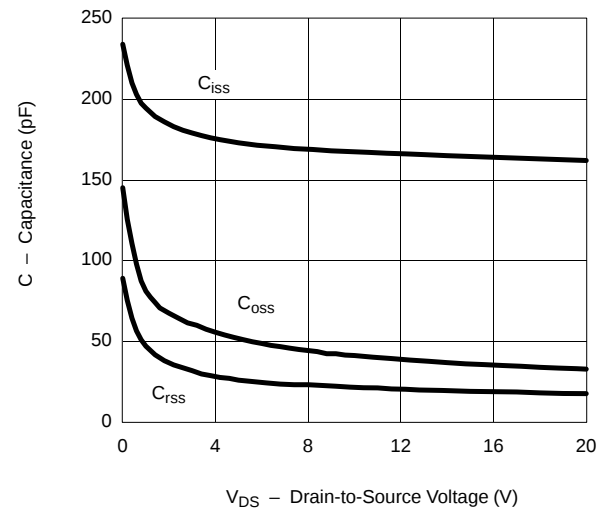
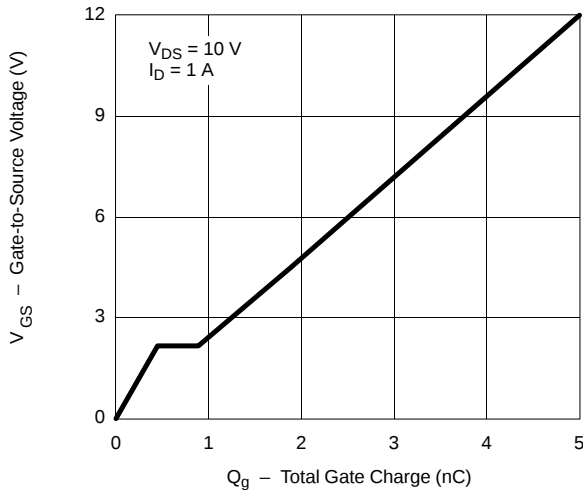
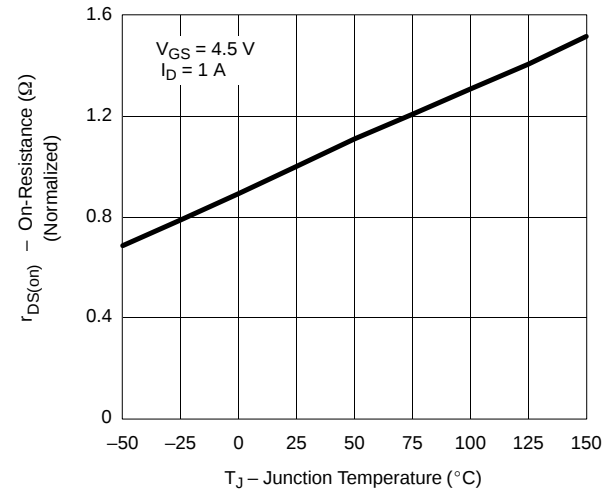
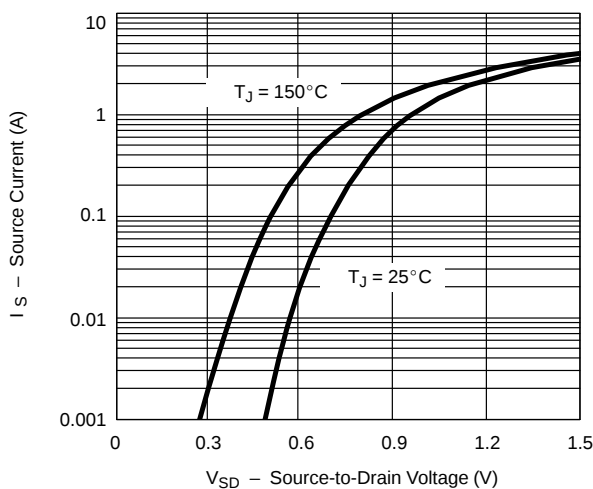
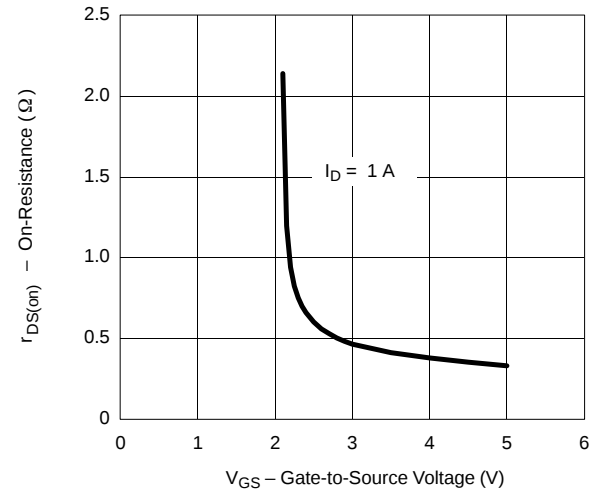
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\ \mu\text{A}$	-0.6			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 4.5\ \text{V}$			± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\ \text{V}$, $V_{GS} = 0\ \text{V}$			-1	μA
		$V_{DS} = -20\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 70^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\ \text{V}$, $V_{GS} = -4.5\ \text{V}$	-2.5			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -4.5\ \text{V}$, $I_D = -1\ \text{A}$		0.360	0.430	Ω
		$V_{GS} = -3.6\ \text{V}$, $I_D = -0.7\ \text{A}$		0.400	0.480	
		$V_{GS} = -2.5\ \text{V}$, $I_D = -0.3\ \text{A}$		0.560	0.700	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\ \text{V}$, $I_D = -1\ \text{A}$		1.7		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1\ \text{A}$, $V_{GS} = 0\ \text{V}$			-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -10\ \text{V}$, $V_{GS} = -4.5\ \text{V}$, $I_D = -1\ \text{A}$		1.9	2.5	nC
Gate-Source Charge	Q_{gs}			0.45		
Gate-Drain Charge	Q_{gd}			0.44		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\ \text{V}$, $R_L = 10\ \Omega$ $I_D \approx -1\ \text{A}$, $V_{GEN} = -4.5\ \text{V}$, $R_G = 6\ \Omega$		180	300	ns
Rise Time	t_r			410	655	
Turn-Off Delay Time	$t_{d(off)}$			560	900	
Fall Time	t_f			530	850	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		435	700	

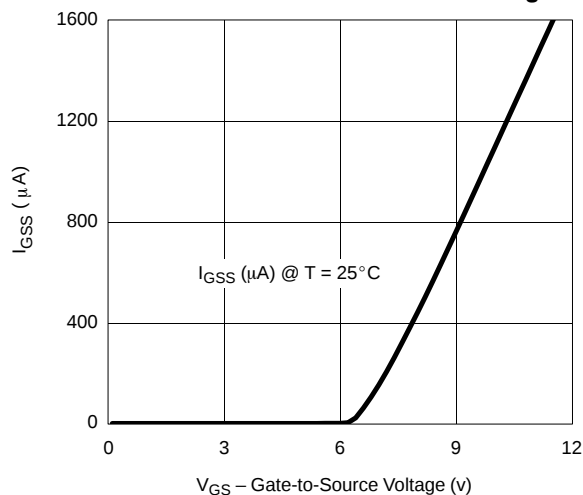
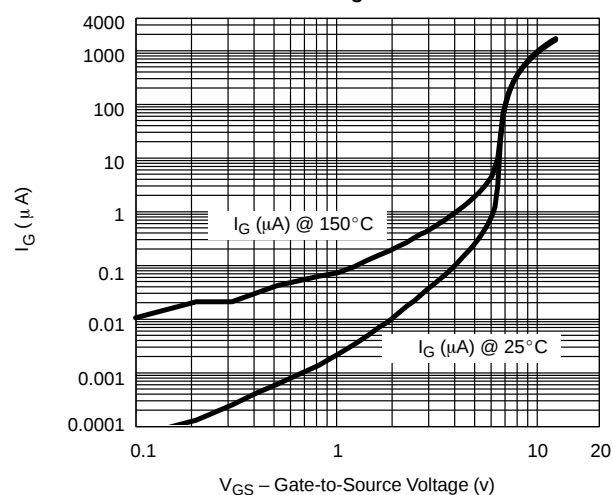
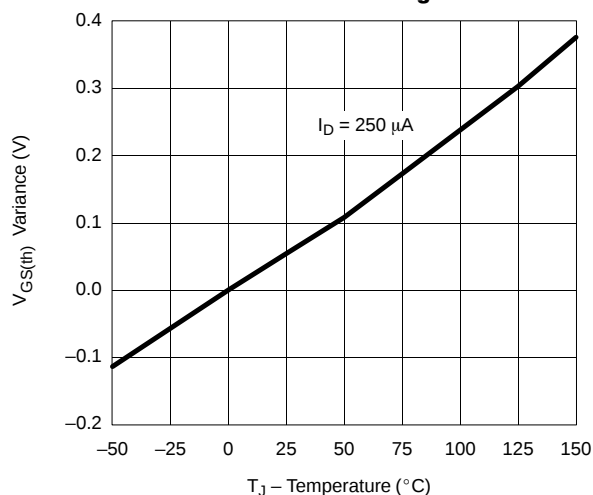
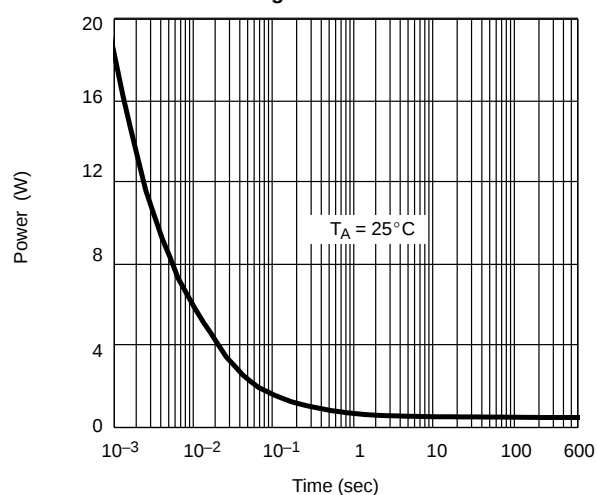
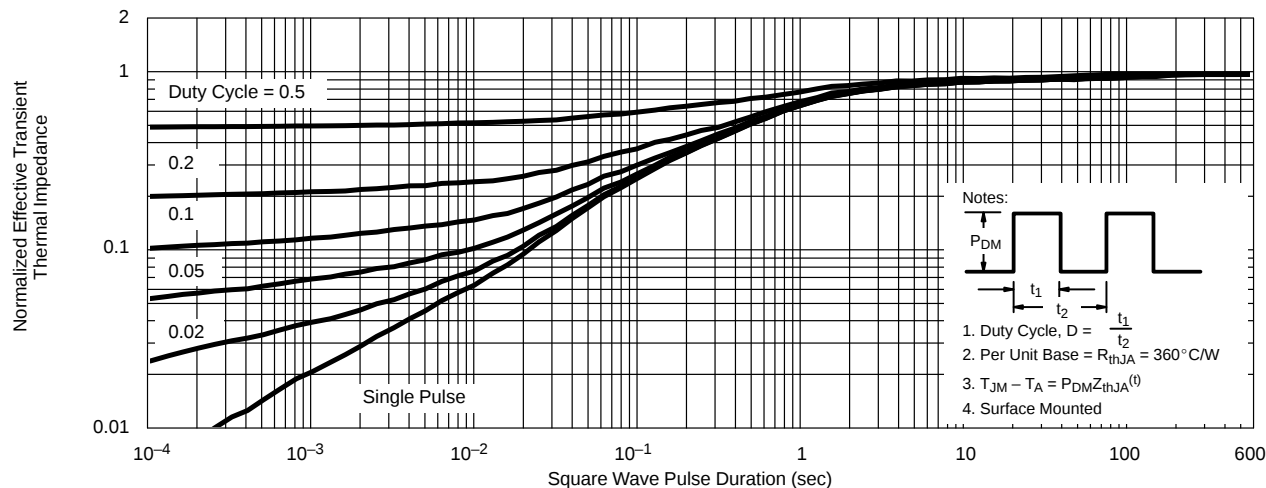
Notes

a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage**

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)
Gate-Current vs. Gate-Source Voltage

Gate-Source Voltage vs. Gate-Current

Threshold Voltage

Single Pulse Power

Normalized Thermal Transient Impedance, Junction-to-Ambient




TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

